

Medium power transistor (−60V, −0.5A)

2SA2090

●Features

- 1) High speed switching. (Tf : Typ. : 35ns at Ic = 500mA)
- 2) Low saturation voltage, typically.
(Typ. : −150mV at Ic = −100mA, Ib = −10mA)
- 3) Strong discharge power for inductive load and capacitance load.
- 4) Complements the 2SC5868.

●Applications

High speed switching, Low noise

●Structure

PNP Silicon epitaxial planar

●Packaging specifications

Type	Package	Taping
	Code	TL
	Basic ordering unit (pieces)	3000
2SA2090		○

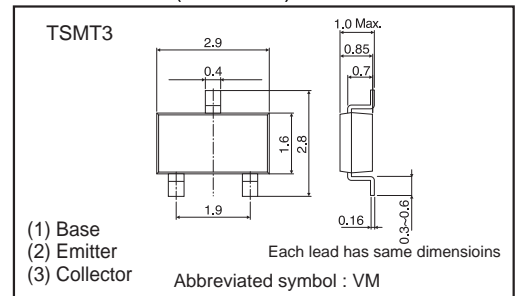
●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V _{CB0}	−60	V
Collector-emitter voltage	V _{CE0}	−60	V
Emitter-base voltage	V _{EB0}	−6	V
Collector current	I _c	−0.5	A
	I _{cP}	−1.0	A ^{*1}
Power dissipation	P _c	500	mW ^{*2}
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	−55 to +150	°C

*1 Pw=10ms

*2 Each terminal mounted on a recommended land.

●Dimensions (Unit : mm)



●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-emitter breakdown voltage	BV_{CEO}	-60	-	-	V	$I_c = -1mA$
Collector-base breakdown voltage	BV_{CBO}	-60	-	-	V	$I_c = -100mA$
Emitter-base breakdown voltage	BV_{EBO}	-6	-	-	V	$I_E = -100\mu A$
Collector cut-off current	I_{CBO}	-	-	-1.0	μA	$V_{CB} = -60V$
Emitter cut-off current	I_{EBO}	-	-	-1.0	μA	$V_{EB} = -4V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	-	-150	-300	mV	$I_c = -100mA, I_B = -10mA$
DC current gain	h_{FE}	120	-	270	-	$V_{CE} = -2V, I_c = -50mA$
Transition frequency	f_T	-	400	-	MHz	$V_{CE} = -10V, I_E = 100mA, f = 10MHz$ *1
Collector output capacitance	C_{ob}	-	10	-	pF	$V_{CB} = -10V, I_E = 0mA, f = 1MHz$
Turn-on time	T_{on}	-	35	-	ns	$I_c = -500mA,$ $I_{B1} = -50mA$
Storage time	T_{stg}	-	100	-	ns	$I_{B2} = 50mA$
Fall time	T_f	-	60	-	ns	$V_{CC} = -25V$ *1

*1 Measured using pulse current

●hFE RANK

Q
120-270

●Electrical characteristic curves

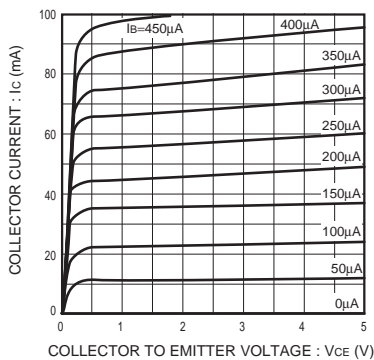


Fig.1 Typical output characteristics

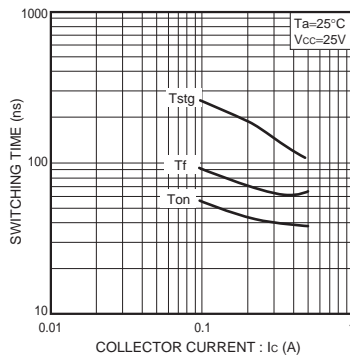


Fig.2 Switching Time

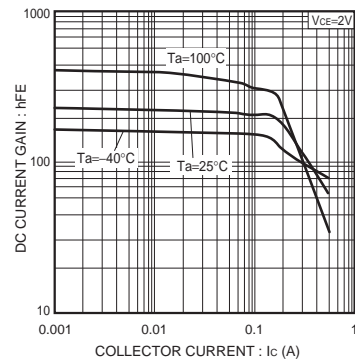


Fig.3 DC current gain vs. collector current (I)

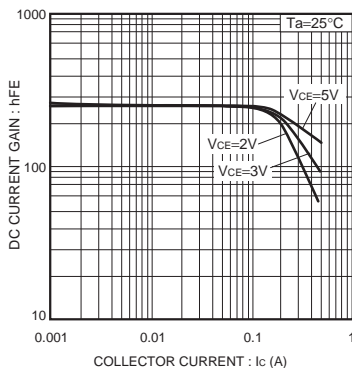


Fig.4 DC current gain vs. collector current (II)

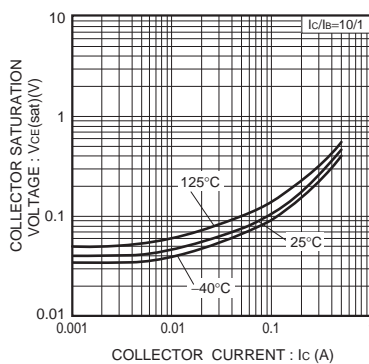


Fig.5 Collector-emitter saturation voltage vs. collector current (I)

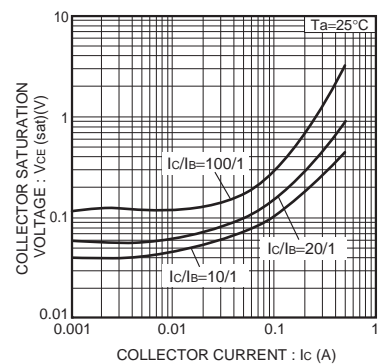


Fig.6 Collector-emitter saturation voltage vs. collector current (II)

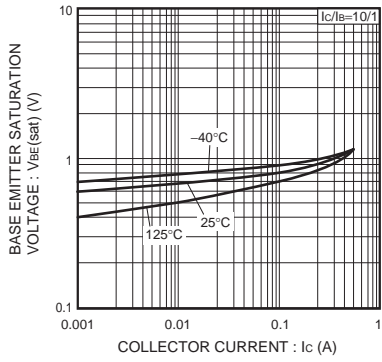


Fig.7 Base-emitter saturation voltage vs. collector current

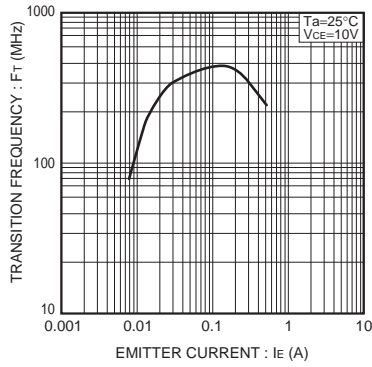


Fig.8 Transition frequency

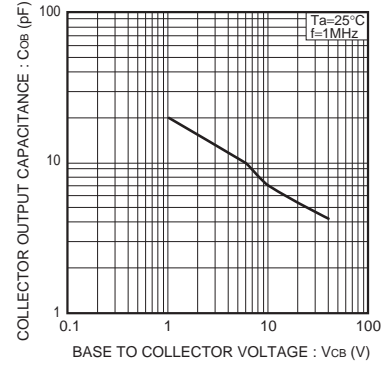


Fig.9 Collector output capacitance

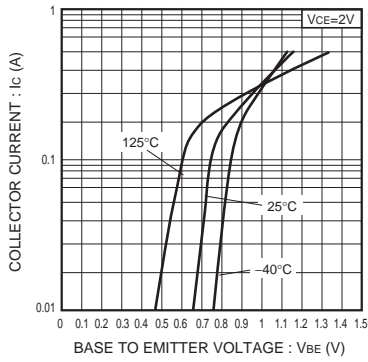
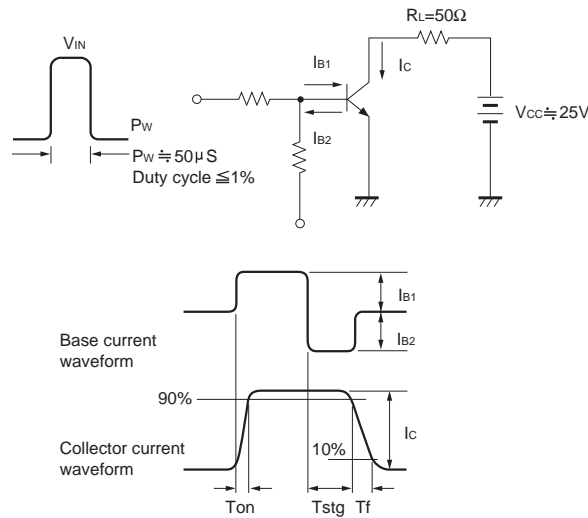


Fig.10 Ground emitter propagation characteristics

●Switching characteristics measurement circuits



Notes

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